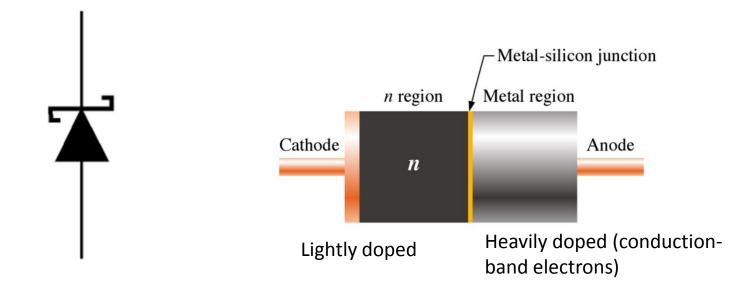
Lecture-4

Schottky Diode

The Schottky diode's (hot-carrier diodes) significant characteristic is its fast switching speed. This is useful for high frequencies and digital applications. It is not a typical diode in that it does not have a p-n junction. Instead, it consists of a lightly-doped n-material and heavily-doped (conduction-band electrons) metal bounded together.

Response is very quick...high speed digital communications.

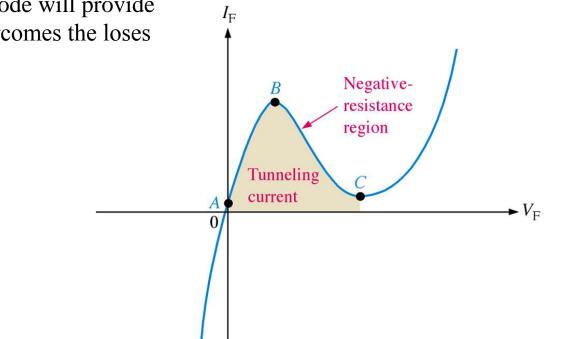


Tunnel Diode

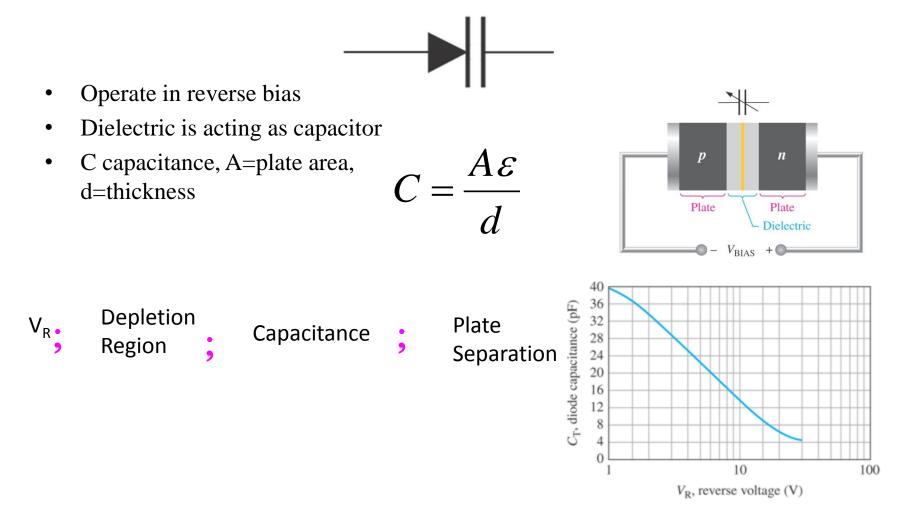
The tunnel diode exhibits negative resistance. It will actually conduct well with low forward bias. With further increases in bias it reaches the negative resistance range where current will actually go down. This is achieved by heavily-doped p and n materials that create a very thin depletion region which permits electrons to "tunnel" thru the barrier region.

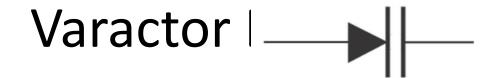
Tank circuits oscillate but "die out" due to the internal resistance. A tunnel diode will provide "negative resistance" that overcomes the loses and maintains the oscillations.

Germanium or Gallium

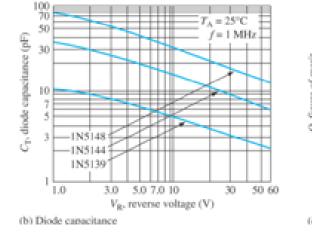


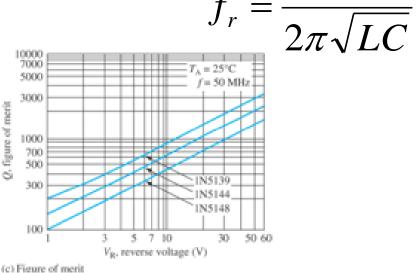
Varactor Diodes





- Tuning Ratio (TR)
 - Nominal Capacitance is typically given (47 pF at $V_R=4 V$)
- Example: 1N5139
- Applications
 - Tuning circuits in TV to set the resonant frequency
 - Bandpass filter (R+(L||C))

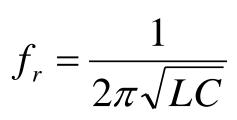


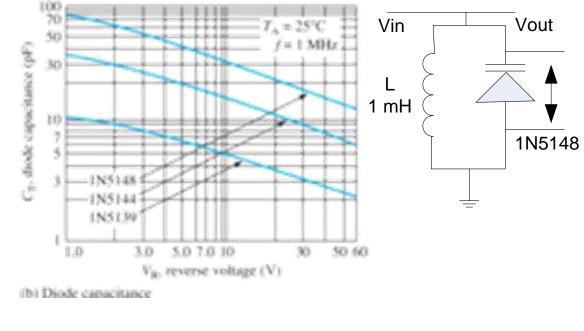


 $TR = \frac{C_{V_R(\min)}}{C_{V_R(\max)}}$

Varactor Diodes Example

- Accume
 - Vcont(min) = 2.9
 - Vcont(max) = 29
- Hence
 - C2.9 = 55 pF
 - C29 = 17 pF





 $f_{min} = 679 \text{ MKhz}$ $f_{max} = 1.22 \text{ MHz}$